

GR-65J075JF: TO-220-FP Cascode GaN HEMT

Description

GR-65J075JF is a normally-off GaN High electron mobility transistor (HEMT) device using the cascode configuration, which provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

Key Specifications

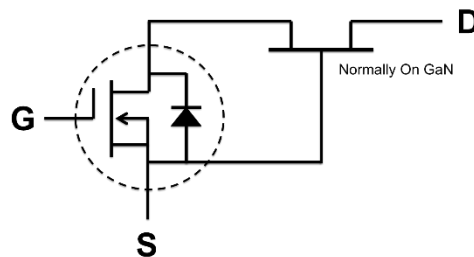
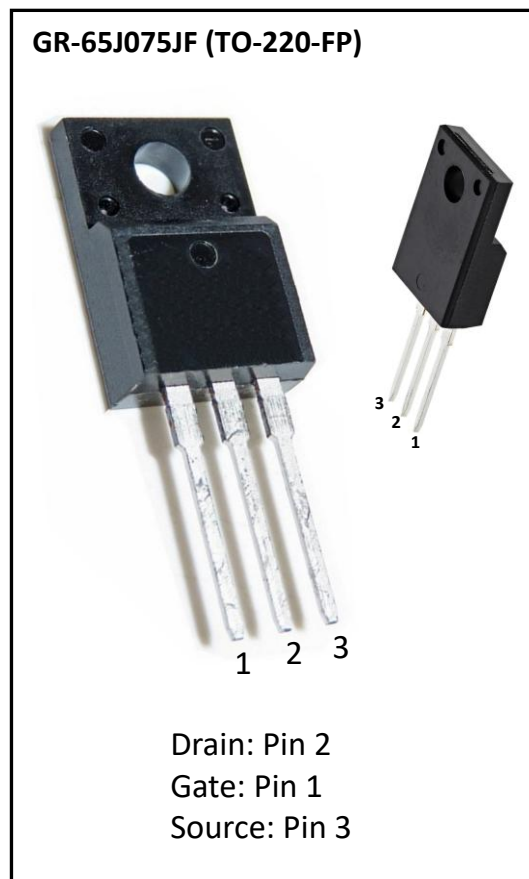
Part Number	GR-65J075JF
V _{DSS}	650V
V _{(TR)DSS}	800V
R _{DS(ON)} , typ.	74mΩ
Q _G , typ.	12.1nC
Package	TO-220-FP

Features

- Gate drive voltage compatibility (-20V to +20V)
- High operating frequency
- Pin to Pin with CoolMOS/SJ and SiC MOSFET
- Low Q_{rr}
- 1.5kV HBM ESD

Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/DC-DC Converters: Boost, Buck, QR Flyback, ACF, AHB, LLC, Half/Full Bridge Application
- Motor Drives, Lighting, Server



Cascode Device Structure

1- Electrical Characteristics

➤ **Table 1 Absolute maximum ratings**

Symbol	Parameter		Value	Unit
V _{DSS}	Drain-source voltage		650	V
V _{(TR)DSS}	Transient drain to source voltage ^a		800	V
V _{GSS}	Gate- source voltage		-20 ~ +20	V
I _D	Drain current (continuous) at T _C = 25°C operation		23.3	A
	Drain current (continuous) at T _C = 100°C operation		14.8	A
I _{D,pulse}	Pulsed drain current (pulse width: 10μs)		87.5	A
P _D	Maximum power dissipation T _c =25 °C		29.7	W
T _C	Operating temperature	Case	-55 to +150	°C
T _J		Junction	-55 to +150	°C
T _S	Storage temperature		-55 to +150	°C
T _{SOLD}	Soldering peak temperature ^b		260	°C
MSL	Moisture sensitivity level		MSL3	

a. In off-state, spike duty cycle D<0.01, spike duration <1μs

b. For 10 sec., 1.6mm from the case

➤ **Table 2 Thermal Characteristics**

Symbol	Parameter	Value	Unit
R _{θJA}	Thermal resistance junction-ambient	63	°C/W
R _{θJC}	Thermal resistance junction-case	4.21	°C/W

Table 3 Electrical Characteristics ($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter	Conditions	Values			Unit
			min.	typ.	max.	
$V_{(BL)DSS}$	Drain-source voltage	$V_{GS}=0V$	650	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_{GS}=V_{DS}, I_D=1mA$	2.0	3.0	4.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS}=10V, I_D=5A, T_J=25\text{ }^{\circ}\text{C}$	-	74	91	m Ω
		$V_{GS}=10V, I_D=5A, T_J=150\text{ }^{\circ}\text{C}$	-	137	-	
I_{DSS}	Drain-source leakage current	$V_{GS}=0V, V_{DS}=650V, T_J=25\text{ }^{\circ}\text{C}$	-	3.0	60	μA
		$V_{GS}=0V, V_{DS}=650V, T_J=150\text{ }^{\circ}\text{C}$	-	15.0	-	
I_{GSS}	Gate-to-source forward leakage current	$V_{GS}=20V$	-	-	100	nA
	Gate-to-source reverse leakage current	$V_{GS}=-20V$	-	-	-100	
C_{ISS}	Input capacitance	$V_{GS}=0V, V_{DS}=400V, f=1MHz$	-	875	-	pF
C_{OSS}	Output capacitance		-	32.1	-	
C_{RSS}	Reverse transfer capacitance		-	2.47	-	
Q_G	Gate charge	$V_{GS}=0\sim 10V, V_{DS}=400V, I_{DS}=5A$	-	12.1	-	nC
Q_{GS}	Gate-source charge		-	2.41	-	
Q_{GD}	Drain-source charge		-	3.92	-	
Q_{OSS}	Output charge	$V_{GS}=0V, V_{DS}=0\sim 400V$	-	51.8	-	
$t_{D(on)}$	Turn-on delay time	$V_{DS}=400V, V_{GS}=0\text{ to }10V, I_{DS}=2A, R_G=25\Omega$	-	12	-	ns
$t_{D(off)}$	Turn-off delay time		-	18	-	
Q_{RR}	Reverse recovery charge	$I_S=5A, V_{DS}=400V$	-	9.0	-	nC

2- Typical Characteristic Curves

Fig 1. On-Region Characteristics

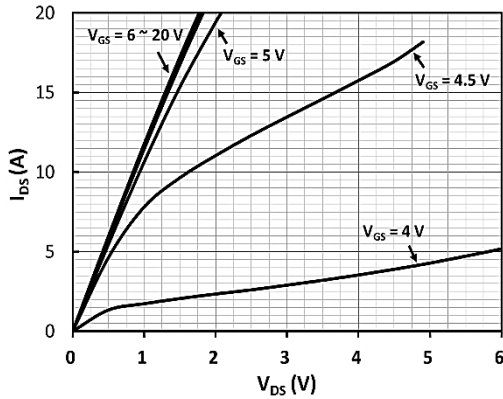


Fig 2. On-Resistance vs Drain Current and Temperature

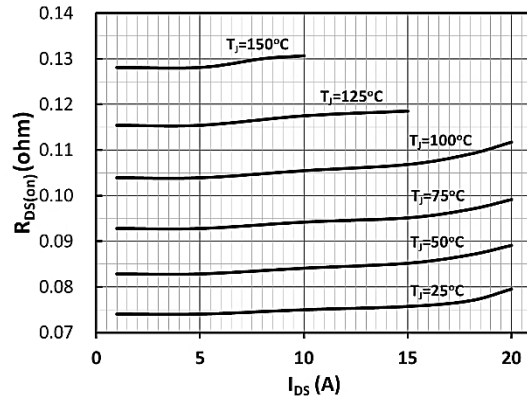


Fig 3. On-Resistance with Drain Current

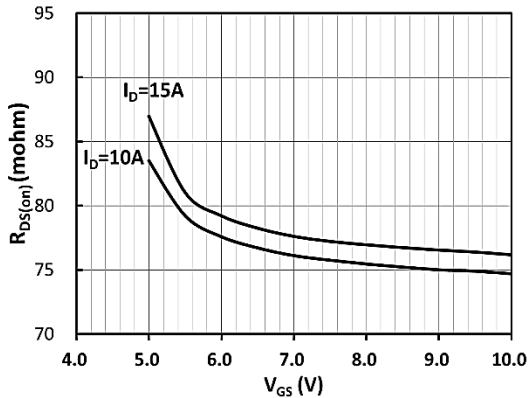


Fig 4. On-Resistance Variation with Temperature

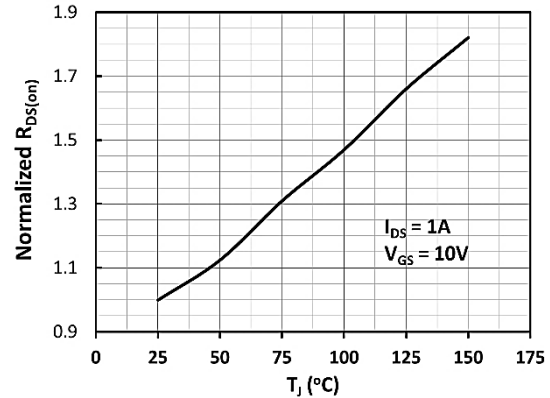


Fig 5. Threshold Voltage with Temperature

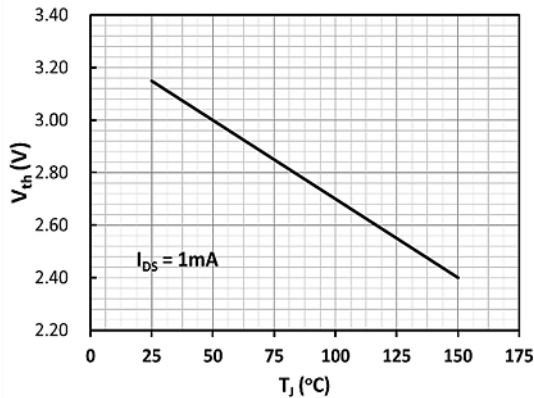


Fig 6. Capacitance Characteristics

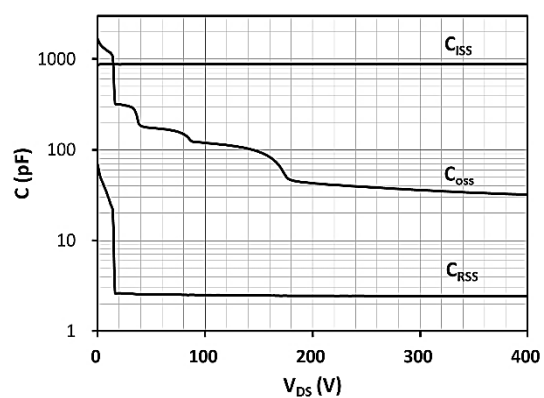


Fig 7. Gate Charge Characteristics, Qg

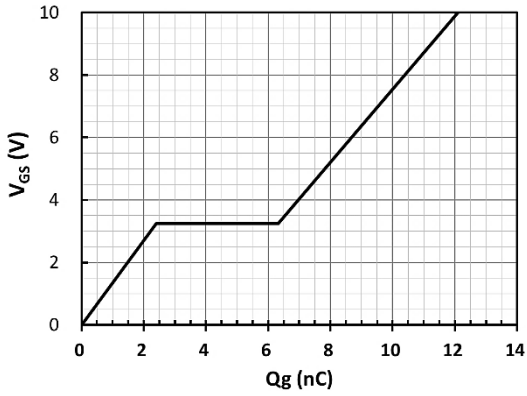


Fig 8. Capacitance Characteristics, Qoss

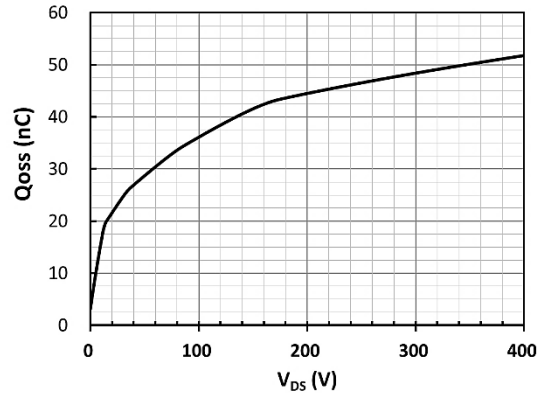
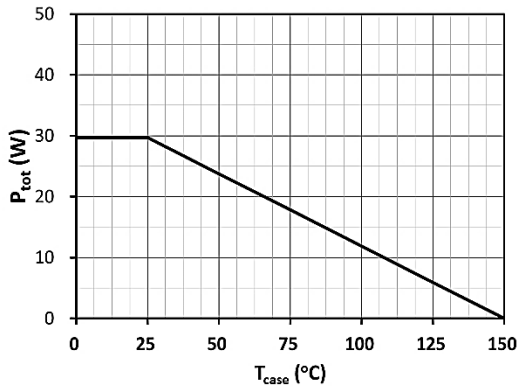
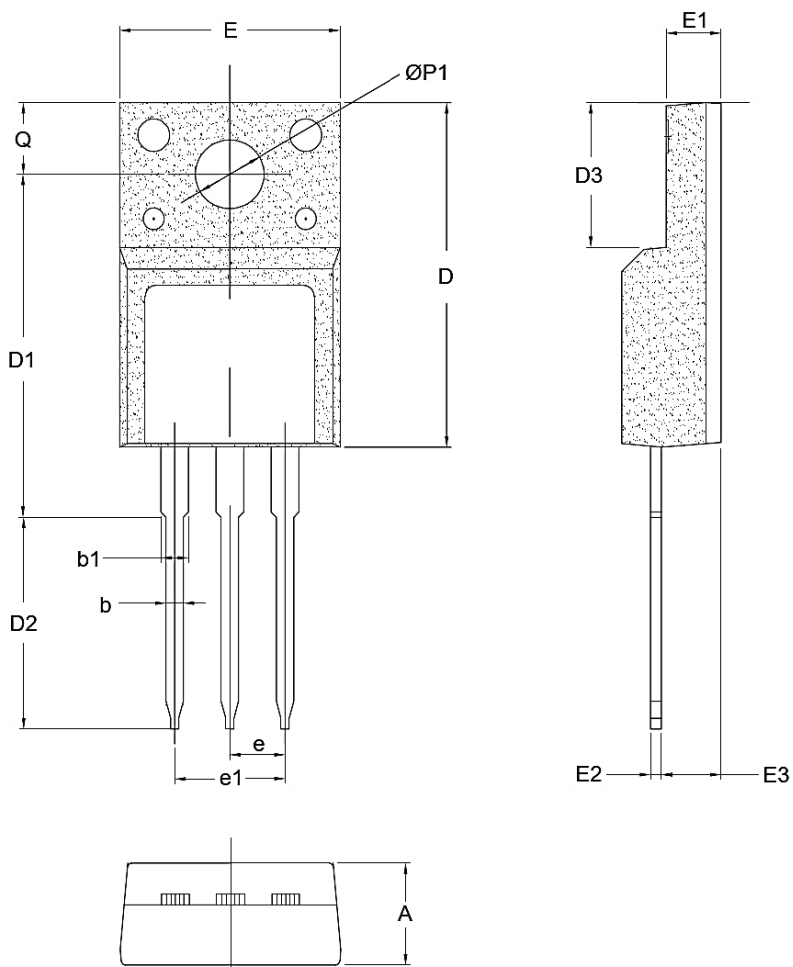


Fig 9. Power Dissipation Derating, Ptot



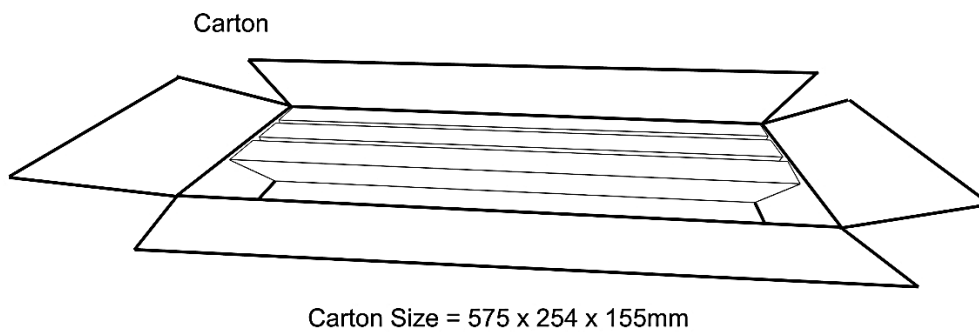
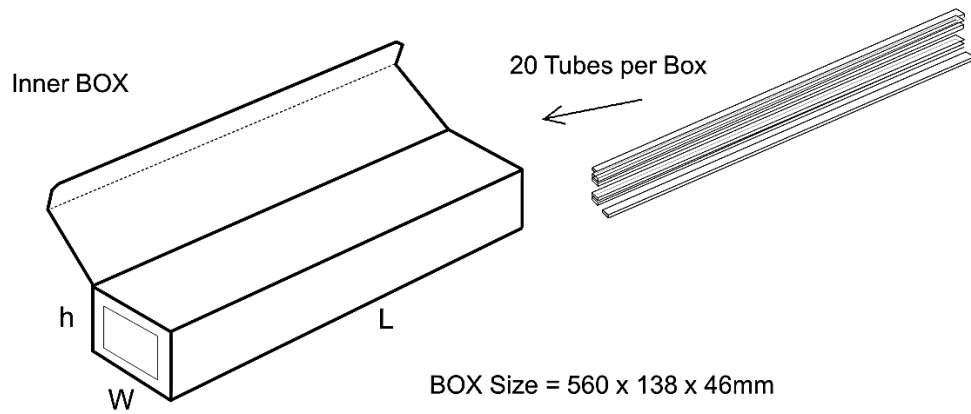
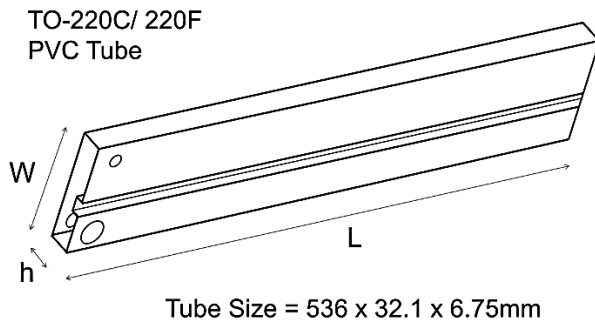
3- Package Outline Dimensions, GR-TO-220-FP



➤ Table 4 Dimension of GR-TO-220-FP

SYMBOL	DIMENSION (IN MM)			SYMBOL	DIMENSION (IN MM)		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	4.40	4.70	5.00	D1	15.5	15.8	16.1
b	1.18	1.28	1.48	D2	9.45	9.75	10.0
b1	0.70	0.80	0.95	D3	6.38	6.68	6.98
e	2.54 BSC			E1	2.24	2.54	2.84
e1	5.08 BSC			E2	0.45	0.50	0.66
D	15.57	15.87	16.17	E3	2.46	2.76	3.06
E	9.86	10.16	10.46	Q	3.00	3.30	3.60
-	-	-	-	φP1	3.22	3.42	3.62

4- Tube Package Information



Package Type	Tube	Inner Box	Carton
TO-220C/ TO-220F	50 EA	1000 EA	5000 EA
-	-	X20 Tube	X5 Box

5- Change Log

Version	Date	Description
01	Nov 28, 2023	Initial version
02	March 27, 2025	Electrical characteristics, Curve and Package information revised
03	April 16, 2026	Electrical characteristics revised

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